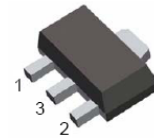
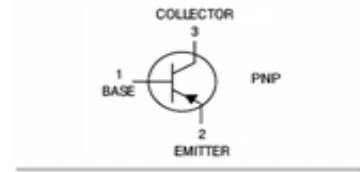


### Features

- Epitaxial planar die construction
- Complimentary to T2SD1664
- Ultra-small surface mount package

HF



SOT-89

### Mechanical Data

- Case: SOT-89
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
2SB1132	SOT-89	1000 pcs / Tape & Reel	BAP/BAQ/BAR

### Maximum Ratings (@ T<sub>A</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	-32	V
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	-5	V
Collector Current (Continuous)	I <sub>C</sub>	-1	A
		-2	

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	500	mW
Thermal Resistance (Junction-to-Ambient)	R <sub>θJA</sub>	250	°C/W
Operating junction Temperature	T <sub>J</sub>	-55 ~ +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	°C

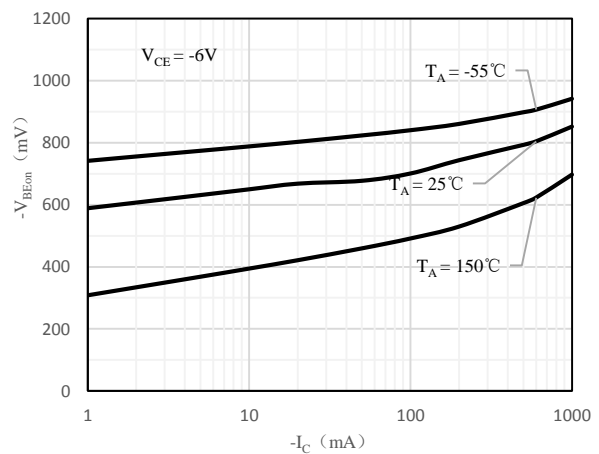
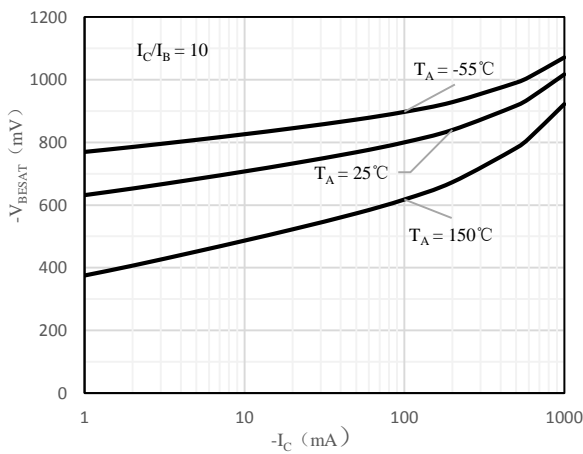
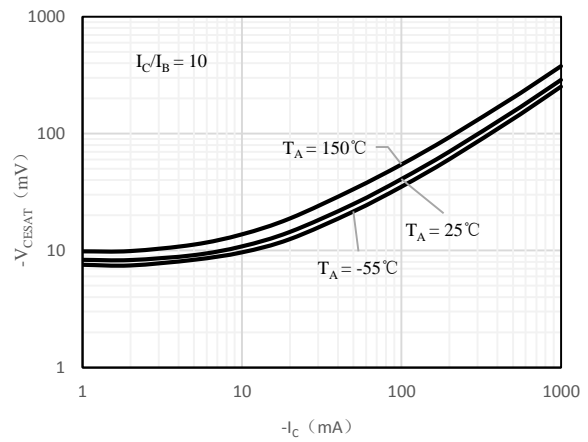
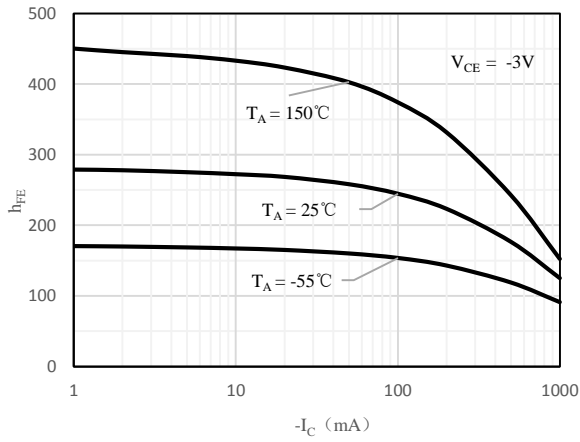
### Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-32	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -20\text{V}, I_E = 0$	-	-	-0.5	$\mu\text{A}$
Collector Cut-off Current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$	-	-	-0.5	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = -3\text{V}, I_C = -100\text{mA}$	82	-	390	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-0.2	-0.5	V
Transition Frequency	$f_T$	$I_C = -50\text{mA}, V_{CE} = -5\text{V}$ $f = 30\text{MHz}$	-	150	-	MHz
Collector Output Capacitance	$C_{OBO}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$	-	20	30	pF

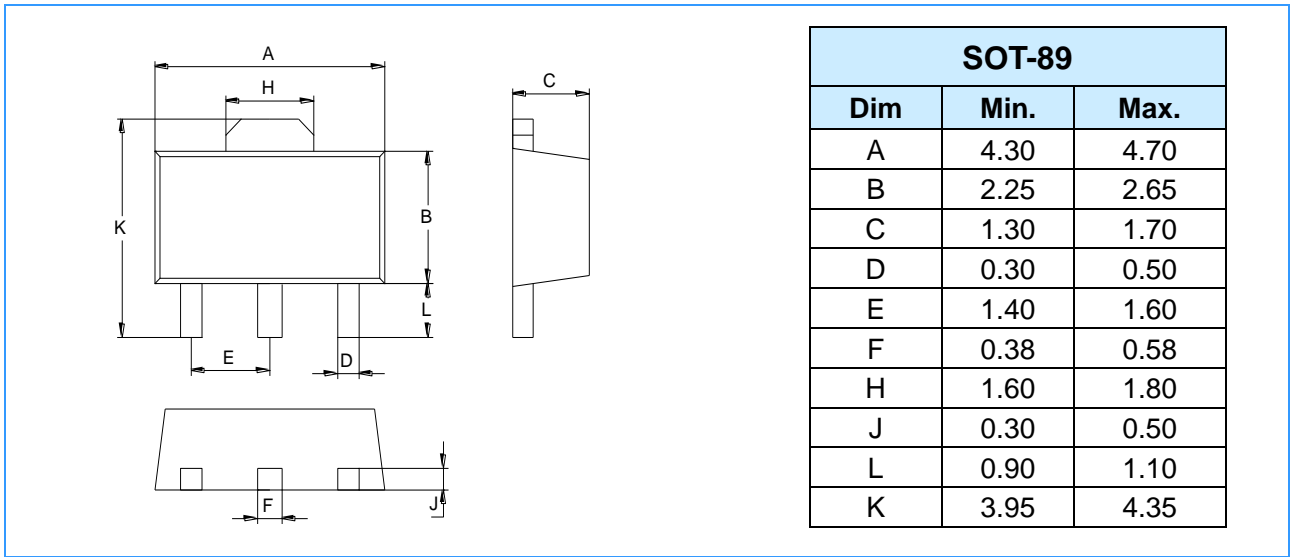
### Classification of $h_{FE}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR

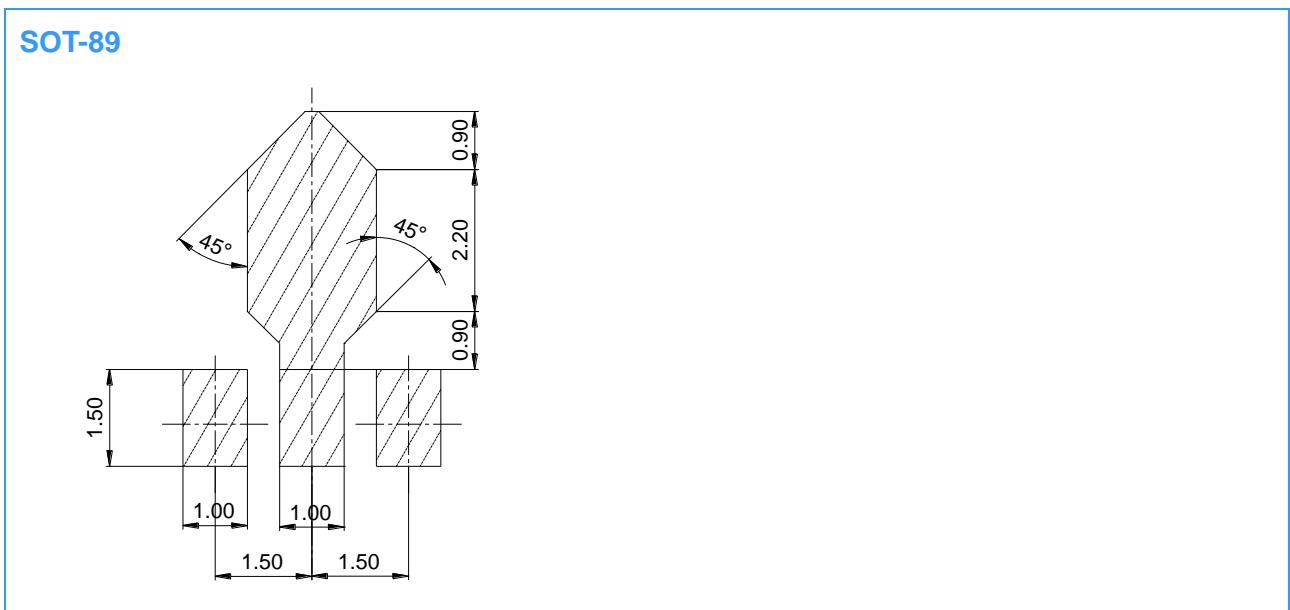
Ratings and Characteristics Curves (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)



**Package Outline Dimensions** (Unit: mm)



**Package Outline Dimensions** (Unit: mm)



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